

2814

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: G. Lippert, et al

Attorney Docket No.: 536-009.002

Application No.: 09/319,699

Group No.: 2814

Filed: July 19, 1999

Examiner: Wille, D. A.



For: SILICON-GERMANIUM HETERO BIPOLAR TRANSISTOR

Director U.S. Patent & Trademark Office
P.O. Box 1450
Alexandria, VA 22313-1450

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INFORMATION DISCLOSURE STATEMENT

Sir:

Applicant submits herewith references of which they are aware, which they believe may be material to the examination of this application and in respect of which they may have a duty to disclose in accordance with 37 CFR 1.56.

While this Information Disclosure Statement may be "material" pursuant to 37 CFR 1.56, it is not intended to constitute an admission that any document referred to herein is "prior art" for this invention unless specifically designated as such.

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined under 37 CFR 1.56(a) exists.

This Information Disclosure Statement is timely since it is certified by the undersigned that each item of information contained in the Information Disclosure Statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Information Disclosure Statement per 37 C.F.R. 1.97(c) and 37 C.F.R. 1.97 (e)(1), therefore the undersigned respectfully submits that no fee is due.

I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to:
Commissioner for Patents, P.O. Box 1450,
Alexandria, VA 22313-1450.

Jodie Droniak 11/12/03
Jodie Droniak Date

Should any fees be due of which the undersigned is unaware, the Commissioner is hereby authorized to charge deposit account 23-0442 any fee deficiency required to submit this IDS.

A PTO-1449 with cited references is enclosed.


Respectfully submitted,

Date: Nov. 12, 2003

Reg. No.: **41,266**


Telephone No.: **(203) 261-1234**

Customer No.: **004955**



James A. Retter

Ware, Fressola, Van Der Sluys &
Adolphson LLP
Bradford Green, Building Five
755 Main Street, P.O. Box 224
Monroe, CT 06468

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT 	ATTY DOCKET NO. 536-009.002	SERIAL NO. 09/319,699
	APPLICANTS: G. Lippert, et al	
	FILING DATE: July 19, 1999	ART UNIT: 2814

UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

	Si Heterojunction Bipolar Transistors, L.D. Lanzerotti; IEDM Technical Digest; International Electronic Devices Meeting; December 11-14, 1994.
	Heterojunction Bipolar Transistors; L.D. Lanzerotti; IEEE; 1996.
	IEDM Technical Digest; International Electronic Devices Meeting; December 8-11, 1996.
	Physics of Semiconductor Devices, 2nd Edition; John Wiley & Sons, Inc., 1981.
	High Speed SiGe-HBT With Very Low Base Sheet Resistivity; E. Kasper; 1993 IEEE.

Examiner	Date:
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FORM PTO-1449
INFORMATION DISCLOSURE STATEMENT



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SERIAL NO.
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		Optimization of SiGe HBT Technology for High Speed Analog and Mixed-Signal Applications; D.L. Hareme; 1993 IEEE.
		2001 IEDM Call for Papers, IEEE International Electron Devices Meeting. (No date provided.)
		2001 IEDM; 2001 IEEE International Electron Devices Meeting; December 3-5, 2001.

Examiner

Date: